

Electrostatically Actuated Cantilever

Introduction

The elastic cantilever beam is an elementary structure in MEMS design. This example shows the bending of a beam due to electrostatic forces. The model uses the electromechanics multiphysics interface to solve the coupled equations for the structural deformation and the electric field. Such structures are frequently tested by means of a low frequency capacitance voltage sweep. The model predicts the results of such a test.

Model Definition

Figure 1 shows the model geometry. The beam has the following dimensions:

 Length: 300 μm • Width: 20 μm • Thickness 2 µm

Because the geometry is symmetric, only half of the beam needs to modeled. The beam is made of polysilicon with a Young's modulus, E, of 153 GPa, and a Poisson's ratio, v, of 0.23. It is fixed at one end but is otherwise free to move. The polysilicon is assumed to be heavily doped, so that electric field penetration into the structure can be neglected. In this case, the Domain Terminal feature can be used to set up the Si domain. The beam resides in an air-filled chamber that is electrically insulated. The lower side of the chamber has a grounded electrode.

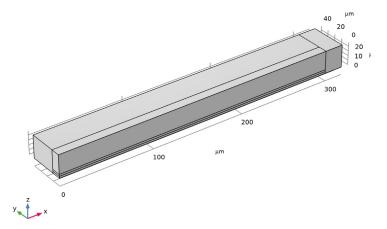


Figure 1: Model Geometry. The beam is 300 μ m long and 2 μ m thick, and it is fixed at x = 0. The model uses symmetry on the zx-plane at y=0. The lower boundary of the surrounding air domain represents the grounded substrate. The model has 20 μ m of free air above and to the sides of the beam, while the gap below the beam is $2 \mu m$.

An electrostatic force caused by an applied potential difference between the two electrodes bends the beam toward the grounded plane beneath it. To compute the electrostatic force, this example calculates the electric field in the surrounding air. The model considers a layer of air 20 µm thick both above and to the sides of the beam, and the air gap between the bottom of the beam and the grounded layer is initially 2 µm. As the beam bends, the geometry of the air gap changes continuously, resulting in a change in the electric field between the electrodes. The coupled physics is handled automatically by the Electromechanics multiphysics interface.

The electrostatic field in the air and in the beam is governed by Poisson's equation:

$$-\nabla \cdot (\varepsilon \nabla V) = 0$$

where derivatives are taken with respect to the spatial coordinates. The numerical model represents the electric potential and its derivatives on a mesh which is moving with respect to the spatial frame. The necessary transformations are taken care of by the Electromechanics multiphysics interface, which also contains smoothing equations governing the movement of the mesh in the air domain.

The cantilever connects to a voltage terminal with a specified bias potential, $V_{\rm in}$. The bottom of the chamber is grounded, while all other boundaries are electrically insulated. The terminal boundary condition automatically computes the capacitance of the system.

The force density that acts on the electrode of the beam results from Maxwell's stress tensor:

$$\mathbf{F}_{\text{es}} = -\frac{1}{2}(\mathbf{E} \cdot \mathbf{D})\mathbf{n} + (\mathbf{n} \cdot \mathbf{E})\mathbf{D}$$

where $\bf E$ and $\bf D$ are the electric field and electric displacement vectors, respectively, and $\bf n$ is the outward normal vector of the boundary. This force is always oriented along the normal of the boundary.

Navier's equations, which govern the deformation of a solid, are more conveniently written in a coordinate system that follows and deforms with the material. In this case, these reference or material coordinates are identical to the actual mesh coordinates.

Results and Discussion

There is positive feedback between the electrostatic forces and the deformation of the cantilever beam. The forces bend the beam and thereby reduce the gap to the grounded substrate. This action, in turn, increases the forces. At a certain voltage the electrostatic forces overcome the stress forces, the system becomes unstable, and the gap collapses. This critical voltage is called the pull-in voltage.

At applied voltages lower than the pull-in voltage, the beam stays in an equilibrium position where the stress forces balance the electrostatic forces. Figure 2 shows the beam displacement and the corresponding displacement of the mesh surrounding it. Figure 3 shows the electric potential and electric field that generates these displacements. In Figure 4 the shape of the cantilever's deflection is illustrated for each applied voltage, by plotting the z-displacement of the underside of the beam at the symmetry boundary. The tip deflection as a function of applied voltage is shown in Figure 5. Note that for applied voltages higher than the pull-in voltage, the solution does not converge because no stable stationary solution exists. This situation occurs if an applied voltage of 6.2 V is tried. The pull-in voltage is therefore between 6.1 V and 6.2 V. For comparison, computations in Ref. 1 predict a pull-in voltage of

$$V_{\mathrm{PI}} = \sqrt{\frac{4c_{1}B}{\varepsilon_{0}L^{4}c_{2}^{2}\left(1+c_{3}\frac{g_{0}}{W}\right)}}$$

where $c_1 = 0.07$, $c_2 = 1.00$, and $c_3 = 0.42$; g_0 is the initial gap between the beam and the ground plane; and

$$B = \hat{E}H^3g_0^3$$

If the beam has a narrow width (W) relative to its thickness (H) and length (L), \hat{E} is Young's modulus, E. Otherwise, E and \hat{E} , the plate modulus, are related by

$$\frac{E}{\hat{E}} \approx 1 - v^2 \left(\frac{(W/L)^{1,37}}{0,5 + (W/L)^{1,37}} \right)^{0.98(L/H)^{-0.056}}$$

where v is Poisson's ratio. Because the calculation in Ref. 1 uses a parallel-plate approximation for calculating the electrostatic force and because it corrects for fringing fields, these results are not directly comparable with those from the simulation. However the agreement is still reasonable: setting $W = 20 \mu m$ results in $V_{\rm PI} = 6.07 \ {\rm V}$.

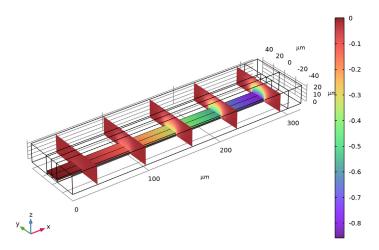


Figure 2: z-displacement for the beam and the moving mesh as a function of position. Each mesh element is depicted as a separate block in the back half of the geometry.

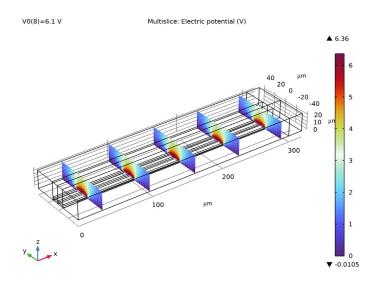


Figure 3: Electric Potential (color) and Electric Field (arrows) at various cross sections through the beam.

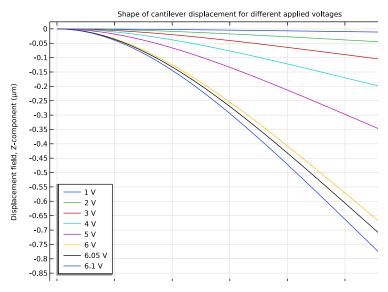


Figure 4: Displacement of the lower surface of the cantilever, plotted along the symmetry boundary, for different values of the applied voltage.

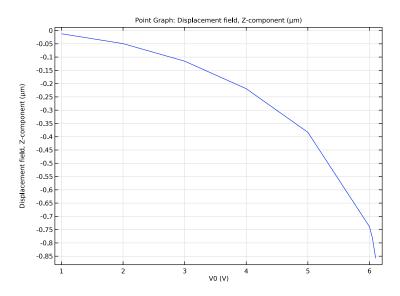


Figure 5: Cantilever tip displacements as a function of applied Voltage V_0 .

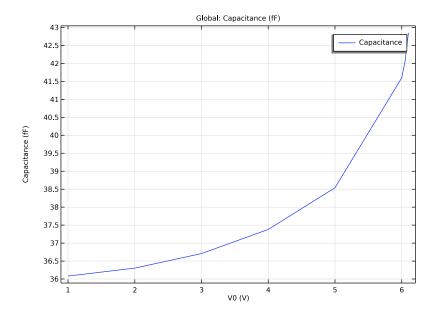


Figure 6: Device capacitance vs applied voltage V_0 .

Figure 6 shows the DC C-V curve predicted for the cantilever beam. To some extent, this is consistent with the behavior of an ideal parallel plate capacitor, whose capacitance increases with decreasing distance between the plates. But this effect does not account for all the change in capacitance observed. In fact, most of it is due to the gradual softening of the coupled electromechanical system. This effect leads to a larger structural response for a given voltage increment at higher bias, which in turn means that more charge must be added to retain the voltage difference between the electrodes.

Reference

1. R.K. Gupta, Electrostatic Pull-In Structure Design for In-Situ Mechanical Property Measurements of Microelectromechanical Systems (MEMS), PhD thesis, MIT, 1997.

Application Library path: MEMS Module/Actuators/ electrostatically_actuated_cantilever

From the File menu, choose New.

NEW

In the New window, click Model Wizard.

MODEL WIZARD

- I In the Model Wizard window, click 3D.
- 2 In the Select Physics tree, select Structural Mechanics > Electromagnetics-Structure Interaction > Electromechanics > Electromechanics, Solid.
- 3 Click Add.
- 4 Click 🗪 Study.
- 5 In the Select Study tree, select General Studies > Stationary.
- 6 Click **Done**.

GEOMETRY I

Use microns to define the geometry units.

- I In the Model Builder window, under Component I (compl) click Geometry I.
- 2 In the Settings window for Geometry, locate the Units section.
- 3 From the Length unit list, choose µm.

Create two blocks to represent the cantilever and air domains, respectively.

Block I (blk I)

- I In the Geometry toolbar, click Block.
- 2 In the Settings window for Block, locate the Size and Shape section.
- 3 In the Width text field, type 300.
- 4 In the **Depth** text field, type 10.
- 5 In the **Height** text field, type 2.
- 6 Locate the **Position** section. In the **z** text field, type 2.
- 7 Click | Build Selected.

Block 2 (blk2)

- I In the Geometry toolbar, click Block.
- 2 In the Settings window for Block, locate the Size and Shape section.
- 3 In the Width text field, type 320.

- 4 In the **Depth** text field, type 40.
- 5 In the Height text field, type 24.

Add two more blocks to simplify meshing of the geometry.

Block 3 (blk3)

- I In the Geometry toolbar, click Block.
- 2 In the Settings window for Block, locate the Size and Shape section.
- 3 In the Width text field, type 20.
- 4 In the **Depth** text field, type 40.
- 5 In the Height text field, type 24.
- 6 Locate the Position section. In the x text field, type 300.

Block 4 (blk4)

- I In the Geometry toolbar, click **Block**.
- 2 In the Settings window for Block, locate the Size and Shape section.
- 3 In the Width text field, type 300.
- 4 In the **Depth** text field, type 10.
- 5 In the Height text field, type 24.
- 6 Click **Build All Objects**.

Add a parameter for the DC voltage applied to the cantilever.

GLOBAL DEFINITIONS

Parameters 1

- I In the Model Builder window, under Global Definitions click Parameters 1.
- 2 In the Settings window for Parameters, locate the Parameters section.
- **3** In the table, enter the following settings:

Name	Expression	Value	Description
V0	5[V]	5 V	Bias on cantilever

The cantilever is assumed to be heavily doped so that it acts as a conductor, held at constant potential. The Linear Elastic Material feature is therefore used.

SOLID MECHANICS (SOLID)

- I In the Model Builder window, under Component I (compl) click Solid Mechanics (solid).
- 2 Select Domain 2 only.

DEFINITIONS

Air

- I In the **Definitions** toolbar, click **Explicit**.
- 2 In the Settings window for Explicit, locate the Input Entities section.
- 3 Click Paste Selection.
- 4 In the Paste Selection dialog, type 1,3,4,5 in the Selection text field.
- 5 Click OK.
- 6 In the Settings window for Explicit, type Air in the Label text field.

MOVING MESH

Deforming Domain I

- I In the Model Builder window, under Component I (compl) > Moving Mesh click Deforming Domain 1.
- 2 In the Settings window for Deforming Domain, locate the Domain Selection section.
- 3 From the Selection list, choose Air.

Fix one end of the cantilever.

SOLID MECHANICS (SOLID)

Fixed Constraint I

- I In the Physics toolbar, click **Boundaries** and choose Fixed Constraint.
- 2 Select Boundary 4 only.

Since only half of the cantilever is included in the model, the symmetry condition should be applied on the midplane of the solid. The electric field default condition (Zero **Charge**) is equivalent to a symmetry condition, so only the structural symmetry boundary condition needs to be applied.

Symmetry I

- I In the Physics toolbar, click **Boundaries** and choose Symmetry.
- 2 Select Boundary 5 only.

MOVING MESH

Symmetry/Roller 1

I In the Model Builder window, under Component I (compl) > Moving Mesh click Symmetry/Roller 1.

2 Select Boundaries 2, 8, and 19 only.

Use the Domain Terminal feature to set the voltage of the cantilever. Note: The Domain Terminal feature will be very handy for a conducting domain with a complex shape and many exterior boundaries - instead of selecting all the boundaries to set up the Ground, Terminal, or Electric Potential boundary condition, we only need to select the domain to specify the Domain Terminal with the same effect. In addition, the computation load is reduced, because the electrostatic degrees of freedom within the Domain Terminal do not need to be solved for.

ELECTROSTATICS (ES)

Charge Conservation in Solids I

In the Model Builder window, under Component I (compl) > Electrostatics (es) right-click Charge Conservation in Solids I and choose Delete.

Terminal I

- I In the Physics toolbar, click **Domains** and choose Terminal.
- 2 Select Domain 2 only.
- 3 In the Settings window for Terminal, locate the Terminal section.
- 4 From the Terminal type list, choose Voltage.
- **5** In the V_0 text field, type V0.

Set up the ground plane underneath the cantilever.

Ground I

- I In the Physics toolbar, click **Boundaries** and choose **Ground**.
- 2 Select Boundaries 3 and 13 only.

Add Materials to the model.

MATERIALS

Material I (mat I)

- I In the Model Builder window, under Component I (compl) right-click Materials and choose Blank Material.
- 2 Select Domain 2 only.
- 3 In the Settings window for Material, locate the Material Contents section.

4 In the table, enter the following settings:

Property	Variable	Value	Unit	Property group
Young's modulus	E	153[GPa]	Pa	Young's modulus and Poisson's ratio
Poisson's ratio	nu	0.23	I	Young's modulus and Poisson's ratio
Density	rho	2330	kg/m³	Basic

MESH I

Mapped I

- I In the Mesh toolbar, click \times More Generators and choose Mapped.
- **2** Select Boundaries 1, 4, and 7 only.

Distribution I

- I Right-click Mapped I and choose Distribution.
- **2** Select Edges 1, 2, 4, 5, 8, 12, and 15 only.
- 3 In the Settings window for Distribution, locate the Distribution section.
- 4 In the Number of elements text field, type 2.

Distribution 2

- I In the Model Builder window, right-click Mapped I and choose Distribution.
- 2 Select Edges 7 and 17 only.
- 3 In the Settings window for Distribution, click Paul Build Selected.

Copy Edge 1

- I In the Model Builder window, right-click Mesh I and choose Copying Operations > Copy Edge.
- 2 Select Edges 12, 15, and 17 only.
- 3 In the Settings window for Copy Edge, locate the Destination Edges section.
- **4** Click to select the **Activate Selection** toggle button.
- **5** Select Edge 21 only.
- 6 Click **Build Selected**.

Mapped 2

- I In the Mesh toolbar, click \textstyle More Generators and choose Mapped.
- 2 Select Boundary 11 only.

Distribution I

- I Right-click Mapped 2 and choose Distribution.
- 2 Select Edges 13 and 19 only.
- 3 In the Settings window for Distribution, click **Build Selected**.

In the Mesh toolbar, click A Swept.

Distribution I

- I Right-click **Swept I** and choose **Distribution**.
- **2** Select Domains 1–4 only.
- 3 In the Settings window for Distribution, locate the Distribution section.
- 4 In the Number of elements text field, type 15.

Distribution 2

- I In the Model Builder window, right-click Swept I and choose Distribution.
- **2** Select Domain 5 only.
- 3 In the Settings window for Distribution, locate the Distribution section.
- 4 In the Number of elements text field, type 1.
- 5 Click **Build All**.

Set up a **Parametric Sweep** over the applied voltage.

STUDY I

Step 1: Stationary

- I In the Model Builder window, under Study I click Step I: Stationary.
- 2 In the Settings window for Stationary, click to expand the Study Extensions section.
- 3 Select the Auxiliary sweep checkbox.
- 4 Click + Add.
- 5 Click Range.
- 6 In the Range dialog, type 1 in the Start text field.
- 7 In the **Step** text field, type 1.
- 8 In the Stop text field, type 6.
- 9 Click Add.

Add points at 6.05 and 6.1 V to the sweep by adding these points after the range statement. The table field should now contain: range(1,1,6) 6.05 6.1.

10 In the Study toolbar, click **Compute**.

RESULTS

Displacement (solid)

Create a mirrored dataset for postprocessing.

Mirror 3D I

- I In the Results toolbar, click More Datasets and choose Mirror 3D.
- 2 In the Settings window for Mirror 3D, locate the Plane Data section.
- 3 From the Plane list, choose zx-planes.

Edit the first default plot to show the z-displacement and the corresponding mesh deformation.

Vertical displacement (solid)

- I In the Model Builder window, under Results click Displacement (solid).
- 2 In the Settings window for 3D Plot Group, type Vertical displacement (solid) in the Label text field.
- 3 Locate the Data section. From the Dataset list, choose Mirror 3D 1.

Volume 1

- I In the Model Builder window, expand the Vertical displacement (solid) node, then click Volume 1.
- 2 In the Settings window for Volume, locate the Expression section.
- **3** In the **Expression** text field, type w.

Slice 1

- I In the Model Builder window, right-click Vertical displacement (solid) and choose Slice.
- 2 In the Settings window for Slice, locate the Expression section.
- **3** In the **Expression** text field, type spatial.w.
- 4 Click to expand the Inherit Style section. From the Plot list, choose Volume 1.
- 5 In the Vertical displacement (solid) toolbar, click Plot.

Edit the second default potential plot.

Electric Potential (es)

- I In the Model Builder window, under Results click Electric Potential (es).
- 2 In the Settings window for 3D Plot Group, locate the Data section.
- 3 From the Dataset list, choose Mirror 3D 1.

Multislice 1

- I In the Model Builder window, expand the Electric Potential (es) node, then click Multislice 1.
- 2 In the Settings window for Multislice, locate the Multiplane Data section.
- 3 Find the x-planes subsection. From the Entry method list, choose Number of planes.
- **4** In the **Planes** text field, type 5.
- 5 Find the y-planes subsection. From the Entry method list, choose Number of planes.
- 6 In the Planes text field, type 0.
- 7 Find the z-planes subsection. From the Entry method list, choose Number of planes.
- 8 In the Planes text field, type 0.

Streamline Multislice 1

- I In the Model Builder window, click Streamline Multislice I.
- 2 In the Settings window for Streamline Multislice, locate the Multiplane Data section.
- 3 Find the x-planes subsection. From the Entry method list, choose Number of planes.
- 4 In the Planes text field, type 5.
- 5 Find the y-planes subsection. From the Entry method list, choose Number of planes.
- 6 In the Planes text field, type 0.
- 7 Find the z-planes subsection. From the Entry method list, choose Number of planes.
- 8 In the Planes text field, type 0.
- 9 Locate the Streamline Positioning section. In the Separating distance text field, type 0.04.
- 10 In the Electric Potential (es) toolbar, click Plot.

Add a plot to show the deformed shape of the underside of the cantilever.

ID Plot Group 5

In the Results toolbar, click \sim ID Plot Group.

Line Graph 1

- I Right-click ID Plot Group 5 and choose Line Graph.
- **2** Select Edge 6 only.
- 3 In the Settings window for Line Graph, click Replace Expression in the upper-right corner of the y-Axis Data section. From the menu, choose Component I (compl) > Solid Mechanics > Displacement > Displacement field - m > w - Displacement field, Zcomponent.

4 Click to expand the **Legends** section. Select the **Show legends** checkbox.

Displacement vs. Applied Voltage

- I In the Model Builder window, click ID Plot Group 5.
- 2 In the Settings window for ID Plot Group, locate the Legend section.
- 3 From the Position list, choose Lower left.
- 4 Click to expand the Title section. From the Title type list, choose Manual.
- 5 In the Title text area, type Shape of cantilever displacement for different applied voltages.
- 6 In the Label text field, type Displacement vs. Applied Voltage.
- 7 In the Displacement vs. Applied Voltage toolbar, click **Plot**. Add a plot of tip displacement versus applied DC voltage.

ID Plot Group 6

In the Results toolbar, click \sim ID Plot Group.

Point Graph 1

- I Right-click ID Plot Group 6 and choose Point Graph.
- **2** Select Point 12 only.
- 3 In the Settings window for Point Graph, click Replace Expression in the upper-right corner of the y-Axis Data section. From the menu, choose Component I (compl) > Solid Mechanics > Displacement > Displacement field - m > w - Displacement field, Zcomponent.

Tip Displacement vs. Applied Voltage

- I In the Model Builder window, under Results click ID Plot Group 6.
- 2 In the Settings window for ID Plot Group, type Tip Displacement vs. Applied Voltage in the Label text field.
- Finally, plot the DC capacitance of the device versus voltage.

ID Plot Group 7

In the **Results** toolbar, click \(\subseteq \) **ID Plot Group**.

Global I

I Right-click ID Plot Group 7 and choose Global.

2 In the Settings window for Global, click Replace Expression in the upper-right corner of the y-Axis Data section. From the menu, choose Component I (compl) > Electrostatics > Terminals > es.CII - Maxwell capacitance - F.

Modify the automatically generated expression to account for the symmetry boundary condition.

3 Locate the **y-Axis Data** section. In the table, enter the following settings:

Expression	Unit	Description
2*es.C11	fF	Capacitance

DC C-V Curve

- I In the Model Builder window, under Results click ID Plot Group 7.
- 2 In the Settings window for ID Plot Group, type DC C-V Curve in the Label text field.
- 3 In the DC C-V Curve toolbar, click Plot.